High Voltage Transistor

PNP Silicon

Features

- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage	V _{CEO}	-150	Vdc
Collector - Base Voltage	V _{CBO}	-160	Vdc
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	Ic	-500	mAdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

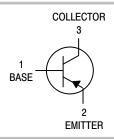
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 2) TA = 25°C	P _D	400	mW
Derate Above 25°C		3.2	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	312	°C/W
Junction and Storage Temperature	T _J , T _{stg}	-55 to +150	°C

- 1. FR-5 @ 100 mm 2 , 0.5 oz. copper traces, still air.
- 2. FR-5 = $1.0 \times 0.75 \times 0.062$ in.



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SC-70 (SOT-323) CASE 419 STYLE 3

MARKING DIAGRAM



4W = Specific Device Code

M = Date Code* ■ Pb–Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]	
MMBT5401WT1G,	SC-70	3000 / Tape &	
NSVMMBT5401WT1G	(Pb-Free)	Reel	

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25$ °C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector – Emitter Breakdown Voltage (I _C = -1.0 mAdc, I _B = 0)	V _{(BR)CEO}	-150	_	Vdc
Collector – Base Breakdown Voltage (I _C = –100 μAdc, I _E = 0)	V _{(BR)CBO}	-160	_	Vdc
Emitter – Base Breakdown Voltage ($I_E = -10 \mu Adc$, $I_C = 0$)	V _{(BR)EBO}	-5.0	_	Vdc
Collector–Base Cutoff Current $(V_{CB} = -120 \text{ Vdc}, I_E = 0)$ $(V_{CB} = -120 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	I _{CBO}	- -	-50 -50	nAdc μAdc
ON CHARACTERISTICS				
DC Current Gain $ \begin{aligned} &(I_C = -1.0 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}) \\ &(I_C = -10 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}) \\ &(I_C = -50 \text{ mAdc}, V_{CE} = -5.0 \text{ Vdc}) \end{aligned} $	h _{FE}	50 60 50	- 240 -	-
Collector – Emitter Saturation Voltage $ \begin{aligned} &(I_C = -10 \text{ mAdc}, I_B = -1.0 \text{ mAdc}) \\ &(I_C = -50 \text{ mAdc}, I_B = -5.0 \text{ mAdc}) \end{aligned} $	V _{CE(sat)}	- -	-0.2 -0.5	Vdc
Base – Emitter Saturation Voltage ($I_C = -10 \text{ mAdc}$, $I_B = -1.0 \text{ mAdc}$) ($I_C = -50 \text{ mAdc}$, $I_B = -5.0 \text{ mAdc}$)	V _{BE(sat)}	- -	-1.0 -1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS				
Current – Gain — Bandwidth Product $(I_C = -10 \text{ mAdc}, V_{CE} = -10 \text{ Vdc}, f = 100 \text{ MHz})$	f _T	100	300	MHz
Output Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}		6.0	pF
Small Signal Current Gain (I _C = -1.0 mAdc, V _{CE} = -10 Vdc, f = 1.0 kHz)	h _{fe}	40	200	-
Noise Figure (I _C = $-200~\mu$ Adc, V _{CE} = $-5.0~\text{Vdc}$, R _S = $10~\Omega$, f = $1.0~\text{kHz}$)	NF	-	8.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

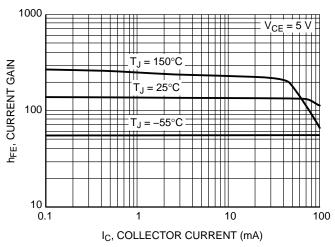


Figure 1. DC Current Gain

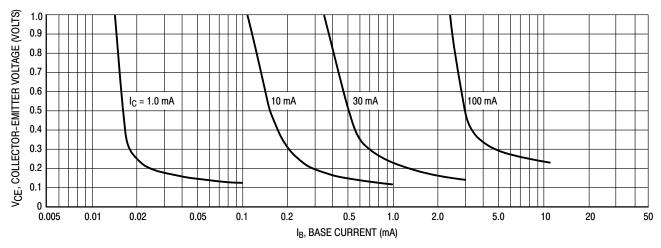


Figure 2. Collector Saturation Region

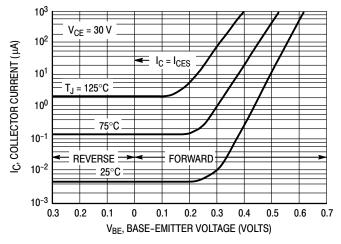


Figure 3. Collector Cut-Off Region

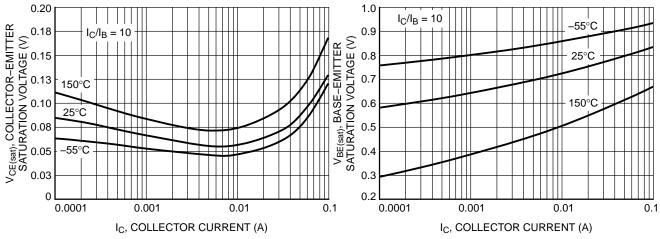


Figure 4. Collector Emitter Saturation Voltage vs. Collector Current

Figure 5. Base Emitter Saturation Voltage vs. Collector Current

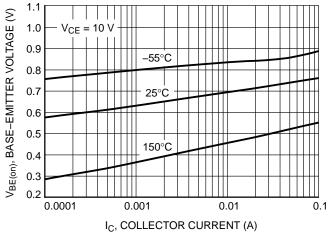


Figure 6. Base Emitter Voltage vs. Collector Current

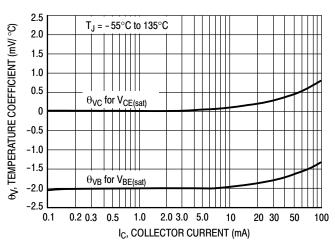


Figure 7. Temperature Coefficients

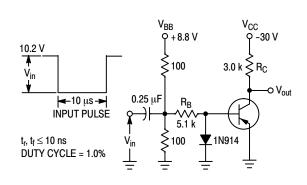


Figure 8. Switching Time Test Circuit

Values Shown are for I_C @ 10 mA

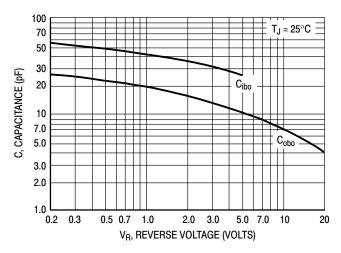
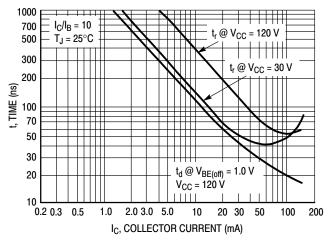


Figure 9. Capacitances



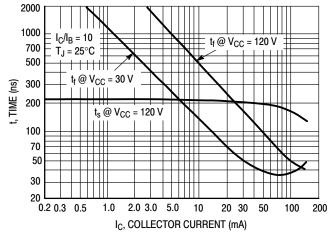
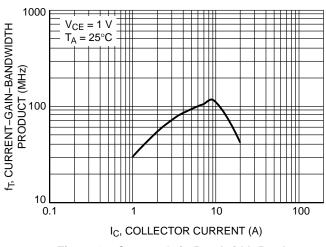


Figure 10. Turn-On Time

Figure 11. Turn-Off Time



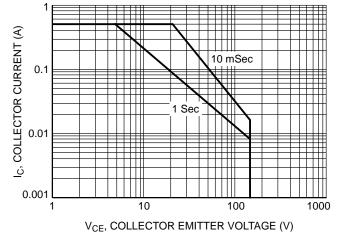
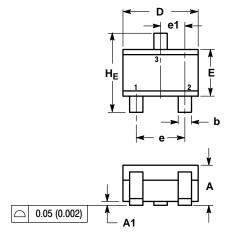


Figure 12. Current Gain Bandwidth Product

Figure 13. Safe Operating Area

PACKAGE DIMENSIONS

SC-70 (SOT-323) CASE 419-04 **ISSUE N**





- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.

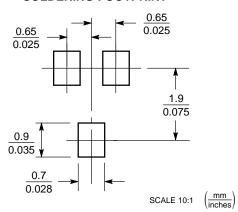
	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 REF	
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1		0.65 BSC			0.026 BSC	;
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3: PIN 1. BASE

EMITTER

3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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